

Silicon TVS diodes Array

Preliminary Data

 ESD / transient protection of e.g. ADSL, VDSL, ISDN, WAN, LAN, I²C Bus, Microcontroller Inputs, Video and other high-speed data lines in telecom applications:

IEC61000-4-2 (ESD): \pm 15 kV (Air / Contact) IEC61000-4-4 (EFT): 4 kV / 80 A (5/50 ns) IEC61000-4-5 (Lightning): 27 A (8/20 μ s)

- Very low capacitance
- Extremly low reverse current < 5 nA
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



DSL70



| Туре | Package | Configuration | Marking |
|--------|---------|-------------------------|---------|
| DSL70* | SOT143 | 2 channel, rail to rail | E4s |

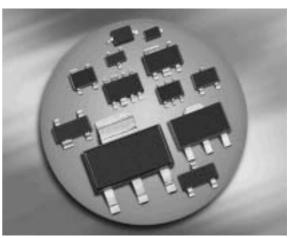
* Preliminary data

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter | Symbol | Value | Unit | | | |
|---|------------------|--------|------|--|--|--|
| ESD contact discharge per diode ¹⁾ | V _{ESD} | 15 | kV | | | |
| Peak pulse current ($t_p = 8 / 20 \ \mu s$) ²⁾ | I _{pp} | 27 | A | | | |
| Peak pulse power (<i>t</i> p = 8 / 20 μs) | P _{pk} | 245 | W | | | |
| Operating temperature range | T _{op} | -55125 | °C | | | |
| Storage temperature | T _{stg} | -65150 | | | | |

 $^{1}V_{\text{ESD}}$ according to IEC61000-4-2

²I_{pp} according to IEC61000-4-5





| Parameter | Symbol | Values | | | Unit |
|--|------------------|--------|------|------|------|
| | | min. | typ. | max. |] |
| Characteristics | | | | | |
| Reverse working voltage | V _{RWM} | - | - | 50 | V |
| Reverse current | / _R | - | - | 5 | nA |
| V _R = 50 V | | | | | |
| Forward clamping voltage ¹⁾ | V _{FC} | | | | V |
| $I_{\rm PP}$ = 1 A, $t_{\rm P}$ = 8/20 µs | | - | 1 | 1.5 | |
| <i>I</i> _{PP} = 10 A, <i>t</i> _P = 8/20 μs | | - | 2.5 | 3 | |
| $I_{\rm PP}$ = 24 A, $t_{\rm P}$ = 8/20 µs | | - | 5 | 6 | |
| <i>I</i> _{PP} = 27 A, <i>t</i> _P = 8/20 μs | | - | 6 | 9 | |
| Diode capacitance | CT | | | | pF |
| V_{R} = 0 V, f = 1 MHz, between I/0 and GND | | - | 2.5 | 5 | |
| V_{R} = 0 V, f = 1 MHz, between I/0 pins | | - | 1.25 | 2.5 | |

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

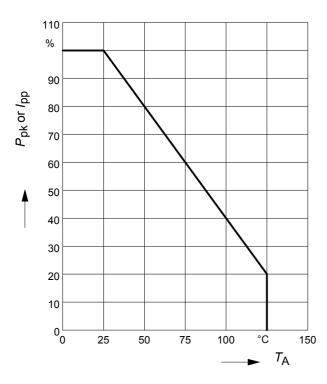
 $^{1}I_{\rm PP}$ according to IEC61000-4-5



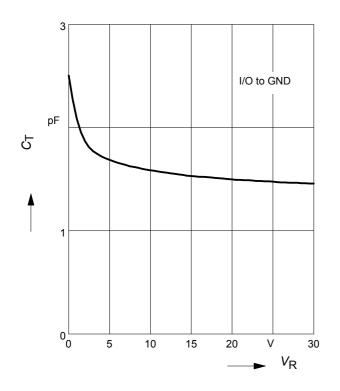
Power derating curve $P_{pk} = f(T_A)$

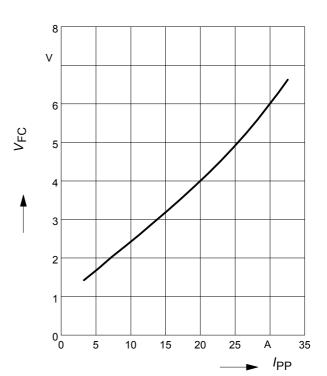


 $t_{\rm p}$ = 8 / 20 µs



Diode capacitance $C_{T} = f(V_{R})$ f = 1MHz

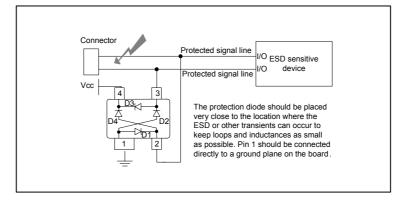




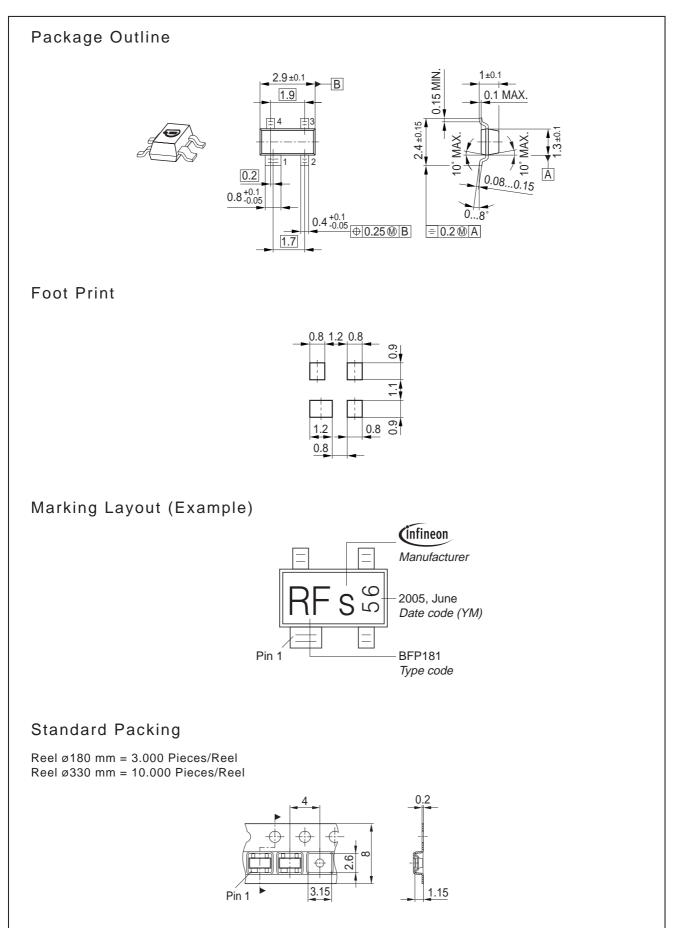


Application example DSL70

dual channel, rail to rail configuration









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